

Search Hist. (6pp) ~~4p~~ (5/30/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	"807413".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 18:43
L2	2	jp-2002226846\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 19:06
L3	41	exfoliati\$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:12
L4	3	exfoliati\$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode)) and AlGaAs and (ITO indium-tin-oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:20
L5	1	exfoliati\$2 near6 AlGaAs and (ITO indium-tin-oxide) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
L6	1	exfoliati\$2 near6 AlGaAs and (ITO indium-tin-oxide) and (372/4\$1. ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
L7	2	(lift-off exfoliati\$2) near6 AlGaAs and (ITO indium-tin-oxide) and (372/4\$1.ccls. 372/50.ccls. 257/79. ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:24
L8	5	(lift-off exfoliati\$2) near6 (aluminum AlGaAs) and (ITO indium-tin-oxide) and (372/4\$1. ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
L9	1	(exfoliati\$2) near6 (aluminum AlGaAs)and (372/4\$1.ccls. 372/50. ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26

L10	1	(exfoliat\$2) near6 (aluminum AlGaAs) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
L11	1	(exfoliat\$2) near6 (aluminum AlGaAs Al AlAs) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:27
L12	131	(exfoliat\$2) near6 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:29
L13	68	(exfoliat\$2) near3 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:34
L14	19	(ITO indium-tin-oxide) near6 (AlGaAs AlAs) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:03
L15	1259	stop adj layer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
L16	2	stop adj layer.ti. and light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
L17	0	(ITO indium-tin-oxide) near6 (AlGaAs:Zn AlGaAs:Si AlGaAs:Ge AlAs:Zn AlAs:Si AlGa:Ge) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:04
L18	0	(ITO indium-tin-oxide) near6 ("AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:04

L19	0	(ITO indium-tin-oxide) near6 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:05
L20	0	(ITO indium-tin-oxide) near10 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
L21	17	(ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
L22	0	(ITO indium-tin-oxide) near10 AlGaAs:Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
L23	1	(ITO indium-tin-oxide) near10 AlGaAs near10 Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:07
L24	1	(ITO indium-tin-oxide) near10 AlGaAs near10 (Si Ge Zn Mg Cd) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:08
L25	0	(ITO indium-tin-oxide) near10 AlGaAs near10 heavily adj doped and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:08
L26	0	(ITO indium-tin-oxide) near10 AlGaAs near10 (n+ "N+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09
L27	0	(ITO indium-tin-oxide) near10 AlGaAs near10 ("n.sub.+" "N.sub.+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09

L28	17	(ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:20
L29	4	ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO transparent) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:25
L30	2	ohmic adj contact near10 (AlAs AlGaAs) near10 (electrode) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:30
L31	0	ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
L32	0	ohmic adj contact near10 (AlAs AlGaAs) near10 zinc adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
L33	106	ohmic adj contact near5 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:32
L34	51	ohmic adj contact near3 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
L35	0	ohmic adj contact near3 (AlAs AlGaAs) and exfoliat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:43
L36	0	(adhesion adhesive) near10 (AlAs AlGaAs) near10 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
L37	5	ohmic adj contact near3 (AlAs AlGaAs) and "10.sup.19"\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:27

L38	53	band adj gap near4 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:54
L39	27	band adj gap near3 ITO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:47
L40	0	direct adj gap near3 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:49
L41	0	direct adj gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
L42	0	direct adj2 gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
L43	6	contact adj resistance near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:00
L44	0	(p-type adj ito) near5 (band adj gap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:06
L45	0	"Al.sub."\$4"Ga.sub."\$4As near10 band adj gap near10 (contact adj region ohmic adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:15
L46	2	"6236065".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
L47	2	"6495862".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35

L48	0	"6495862".pn. and AlGa _N	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
L49	1	"6495862".pn. and exfoliat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:37
L50	1	"6495862".pn. and exfoliat\$3 and (AlGaAs AlGa _N Al aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:50
L51	690	contact adj (region layer) near6 (impurity adj concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51
L52	22	contact adj (region layer) near4 (impurity adj concentration) and transparent adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51